

isc Silicon PNP Power Transistor

2SA2120

DESCRIPTION

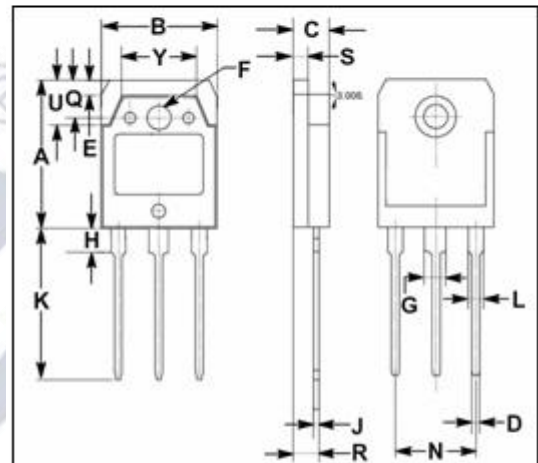
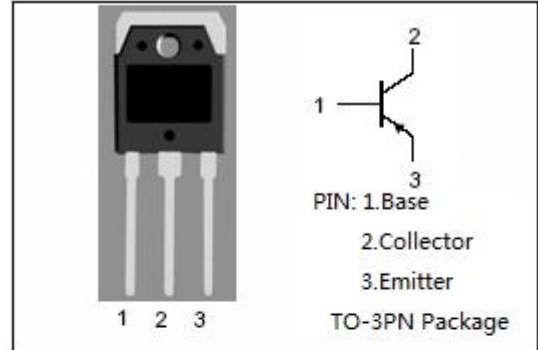
- Recommended for audio frequency amplifier output stage
- Complementary to 2SC5948
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CEO}	Collector-Base Voltage	-200	V
V _{CEO}	Collector-Emitter Voltage	-200	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-12	A
I _{CM}	Collector Current-Pulse	-24	A
P _C	Collector Power Dissipation @T _a =25°C	4.0	W
	Collector Power Dissipation @T _C =25°C	200	
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc Silicon PNP Power Transistor**2SA2120****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA ; I _B = 0	-200			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -8A; I _B = -800mA			-3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -7A ; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -200V ; I _E =0			-5	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C =0			-5	uA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -5V	55		160	
h _{FE-2}	DC Current Gain	I _C = -7A; V _{CE} = -5V	35			

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